Renesas Electronics America Inc - R5F104MGAFB#V0 Datasheet

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What is "Embedded - Microcontrollers"?

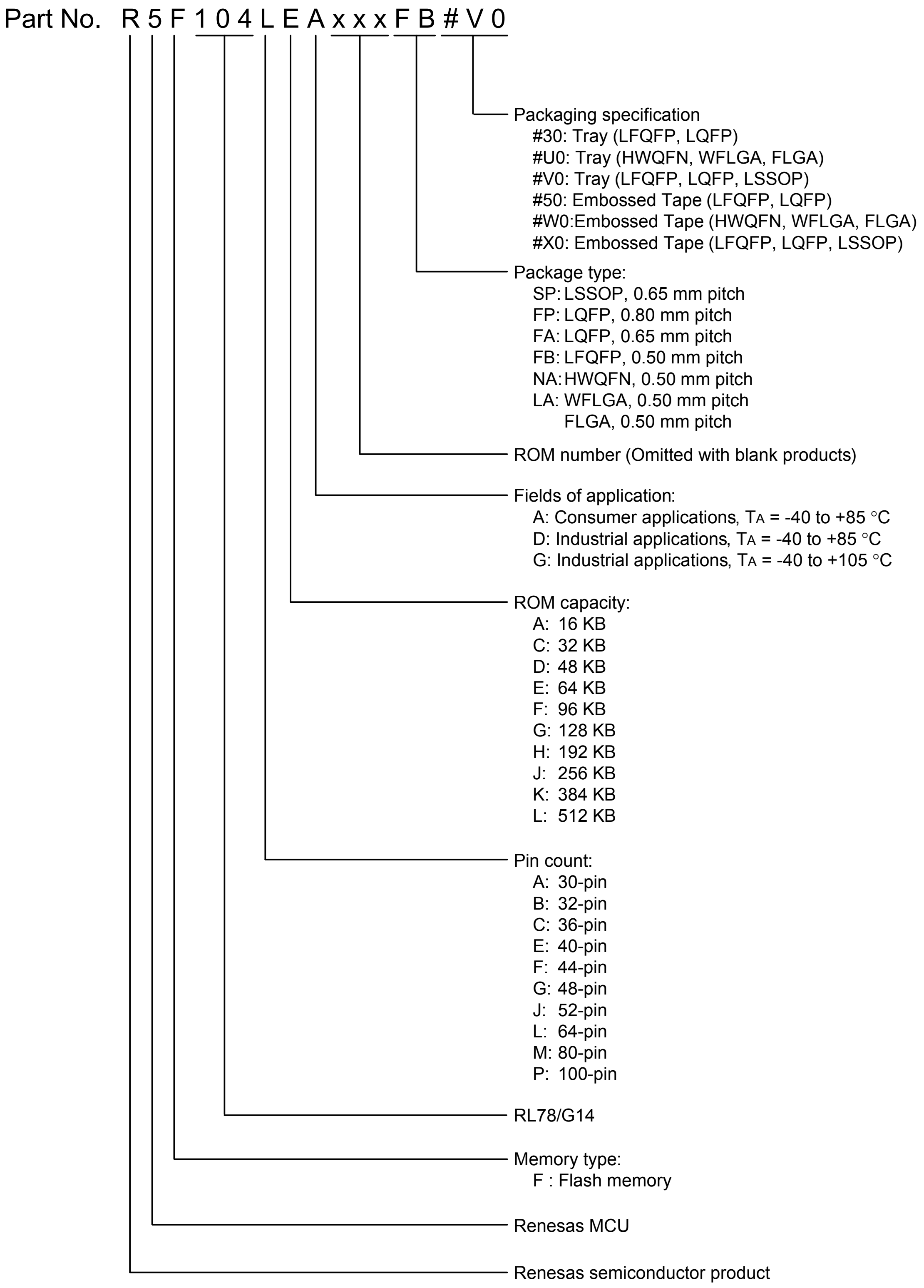
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	64
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 17x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LFQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104mgafb-v0

1.2 Ordering Information

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14



Part No. R 5 F 1 0 4 L E A x x x F B # V 0

Packaging specification
- #30: Tray (LFQFP, LQFP)
- #U0: Tray (HWQFN, WFLGA, FLGA)
- #V0: Tray (LFQFP, LQFP, LSSOP)
- #50: Embossed Tape (LFQFP, LQFP)
- #W0:Embossed Tape (HWQFN, WFLGA, FLGA)
- #X0: Embossed Tape (LFQFP, LQFP, LSSOP)

Package type:
- SP: LSSOP, 0.65 mm pitch
- FP: LQFP, 0.80 mm pitch
- FA: LQFP, 0.65 mm pitch
- FB: LFQFP, 0.50 mm pitch
- NA: HWQFN, 0.50 mm pitch
- LA: WFLGA, 0.50 mm pitch
  FLGA, 0.50 mm pitch

ROM number (Omitted with blank products)

Fields of application:
- A: Consumer applications, T_A = -40 to +85 °C
- D: Industrial applications, T_A = -40 to +85 °C
- G: Industrial applications, T_A = -40 to +105 °C

ROM capacity:
- A: 16 KB
- C: 32 KB
- D: 48 KB
- E: 64 KB
- F: 96 KB
- G: 128 KB
- H: 192 KB
- J: 256 KB
- K: 384 KB
- L: 512 KB

Pin count:
- A: 30-pin
- B: 32-pin
- C: 36-pin
- E: 40-pin
- F: 44-pin
- G: 48-pin
- J: 52-pin
- L: 64-pin
- M: 80-pin
- P: 100-pin

RL78/G14

Memory type:
- F : Flash memory

Renesas MCU

Renesas semiconductor product

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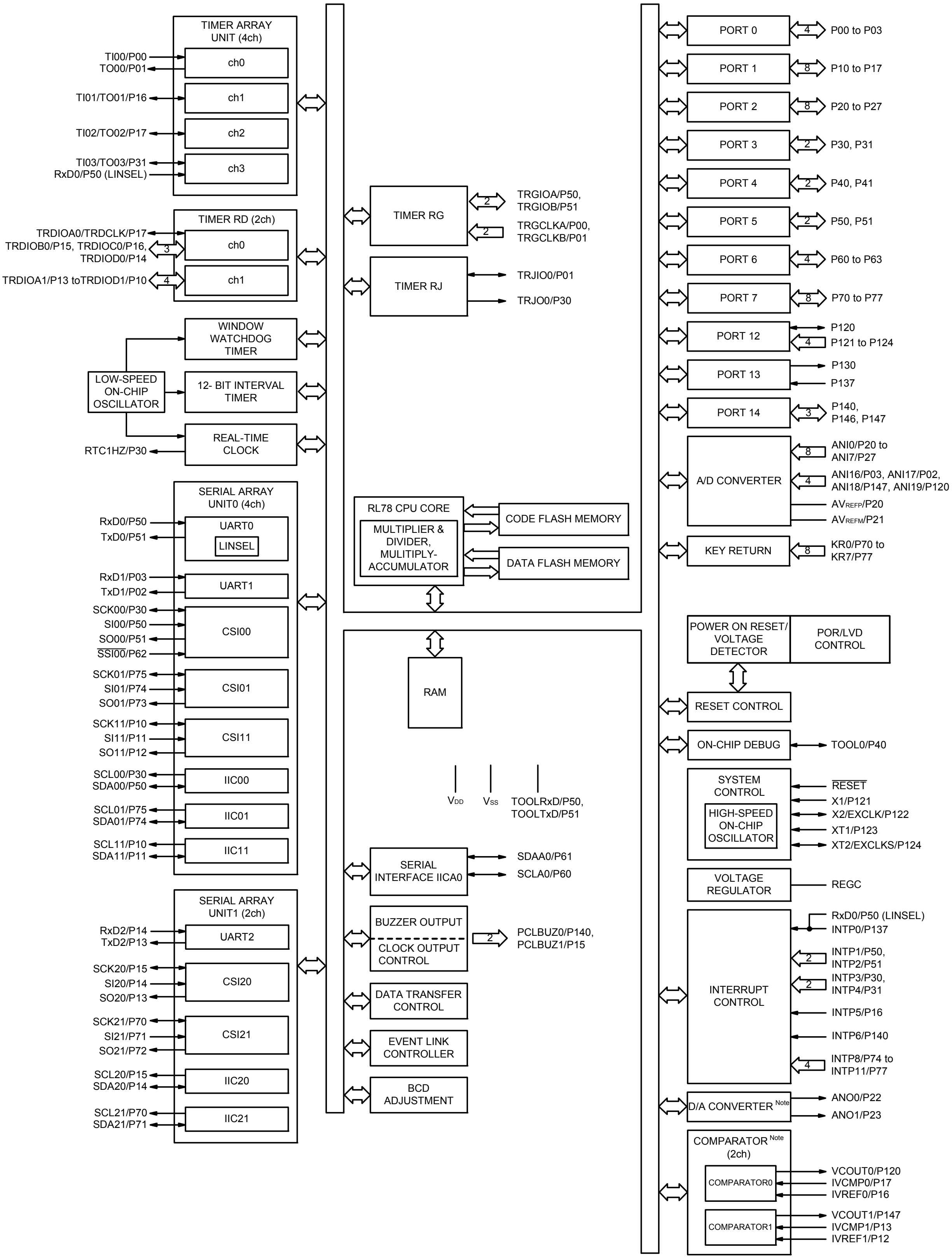
Pin count	Package	Fields of Application Note	Ordering Part Number
30 pins	30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	A	R5F104AAASP#V0, R5F104ACASP#V0, R5F104ADASP#V0, R5F104AEASP#V0, R5F104AFASP#V0, R5F104AGASP#V0 R5F104AAASP#X0, R5F104ACASP#X0, R5F104ADASP#X0, R5F104AEASP#X0, R5F104AFASP#X0, R5F104AGASP#X0
		D	R5F104AADSP#V0, R5F104ACDSP#V0, R5F104ADDSP#V0, R5F104AEDSP#V0, R5F104AFDSP#V0, R5F104AGDSP#V0 R5F104AADSP#X0, R5F104ACDSP#X0, R5F104ADDSP#X0, R5F104AEDSP#X0, R5F104AFDSP#X0, R5F104AGDSP#X0
		G	R5F104AAGSP#V0, R5F104ACGSP#V0, R5F104ADGSP#V0, R5F104AEGSP#V0, R5F104AFGSP#V0, R5F104AGGSP#V0 R5F104AAGSP#X0, R5F104ACGSP#X0, R5F104ADGSP#X0, R5F104AEGSP#X0, R5F104AFGSP#X0, R5F104AGGSP#X0
32 pins	32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)	A	R5F104BAANA#U0, R5F104BCANA#U0, R5F104BDANA#U0, R5F104BEANA#U0, R5F104BFANA#U0, R5F104BGANA#U0 R5F104BAANA#W0, R5F104BCANA#W0, R5F104BDANA#W0, R5F104BEANA#W0, R5F104BFANA#W0, R5F104BGANA#W0
		D	R5F104BADNA#U0, R5F104BCDNA#U0, R5F104BDDNA#U0, R5F104BEDNA#U0, R5F104BFDNA#U0, R5F104BGDNA#U0 R5F104BADNA#W0, R5F104BCDNA#W0, R5F104BDDNA#W0, R5F104BEDNA#W0, R5F104BFDNA#W0, R5F104BGDNA#W0
		G	R5F104BAGNA#U0, R5F104BCGNA#U0, R5F104BDGNA#U0, R5F104BEGNA#U0, R5F104BFGNA#U0, R5F104BGGNA#U0 R5F104BAGNA#W0, R5F104BCGNA#W0, R5F104BDGNA#W0, R5F104BEGNA#W0, R5F104BFGNA#W0, R5F104BGGNA#W0
	32-pin plastic LQFP (7 × 7, 0.8 mm pitch)	A	R5F104BAAFP#V0, R5F104BCAFP#V0, R5F104BDAFP#V0, R5F104BEAFP#V0, R5F104BFAFP#V0, R5F104BGAFP#V0 R5F104BAAFP#X0, R5F104BCAFP#X0, R5F104BDAFP#X0, R5F104BEAFP#X0, R5F104BFAFP#X0, R5F104BGAFP#X0
		D	R5F104BADFP#V0, R5F104BCDFP#V0, R5F104BDDFP#V0, R5F104BEDFP#V0, R5F104BFDFP#V0, R5F104BGDFP#V0 R5F104BADFP#X0, R5F104BCDFP#X0, R5F104BDDFP#X0, R5F104BEDFP#X0, R5F104BFDFP#X0, R5F104BGDFP#X0
		G	R5F104BAGFP#V0, R5F104BCGFP#V0, R5F104BDGFP#V0, R5F104BEGFP#V0, R5F104BFGFP#V0, R5F104BGGFP#V0 R5F104BAGFP#X0, R5F104BCGFP#X0, R5F104BDGFP#X0, R5F104BEGFP#X0, R5F104BFGFP#X0, R5F104BGGFP#X0
36 pins	36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)	A	R5F104CAALA#U0, R5F104CCALA#U0, R5F104CDALA#U0, R5F104CEALA#U0, R5F104CFALA#U0, R5F104CGALA#U0 R5F104CAALA#W0, R5F104CCALA#W0, R5F104CDALA#W0, R5F104CEALA#W0, R5F104CFALA#W0, R5F104CGALA#W0
		G	R5F104CAGLA#U0, R5F104CCGLA#U0, R5F104CDGLA#U0, R5F104CEGLA#U0, R5F104CFGLA#U0, R5F104CGGLA#U0 R5F104CAGLA#W0, R5F104CCGLA#W0, R5F104CDGLA#W0, R5F104CEGLA#W0, R5F104CFGLA#W0, R5F104CGGLA#W0

Note For the fields of application, refer to **Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.5.7 52-pin products



Note Mounted on the 96 KB or more code flash memory products.

[44-pin, 48-pin, 52-pin, 64-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item		44-pin	48-pin	52-pin	64-pin
		R5F104Fx (x = F to H, J)	R5F104Gx (x = F to H, J)	R5F104Jx (x = F to H, J)	R5F104Lx (x = F to H, J)
Code flash memory (KB)		96 to 256	96 to 256	96 to 256	96 to 256
Data flash memory (KB)		8	8	8	8
RAM (KB)		12 to 24 Note	12 to 24 Note	12 to 24 Note	12 to 24 Note
Address space		1 MB			
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)			
	High-speed on-chip oscillator clock (f_{IH})	HS (high-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)			
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz			
Low-speed on-chip oscillator clock		15 kHz (TYP.): V_{DD} = 1.6 to 5.5 V			
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)			
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator clock: f_{IH} = 32 MHz operation)			
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)			
		30.5 μs (Subsystem clock: f_{SUB} = 32.768 kHz operation)			
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.			
I/O port	Total	40	44	48	58
	CMOS I/O	31	34	38	48
	CMOS input	5	5	5	5
	CMOS output	—	1	1	1
	N-ch open-drain I/O (6 V tolerance)	4	4	4	4
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)			
	Watchdog timer	1 channel			
	Real-time clock (RTC)	1 channel			
	12-bit interval timer	1 channel			
	Timer output	Timer outputs: 14 channels PWM outputs: 9 channels			
	RTC output	1 • 1 Hz (subsystem clock: f_{SUB} = 32.768 kHz)			

(**Note** is listed on the next page.)

[80-pin, 100-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item		80-pin	100-pin
		R5F104Mx (x = F to H, J)	R5F104Px (x = F to H, J)
Code flash memory (KB)		96 to 256	96 to 256
Data flash memory (KB)		8	8
RAM (KB)		12 to 24 Note	12 to 24 Note
Address space		1 MB	
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)	
	High-speed on-chip oscillator clock (f_{IH})	HS (high-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)	
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz	
Low-speed on-chip oscillator clock		15 kHz (TYP.): V_{DD} = 1.6 to 5.5 V	
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)	
Minimum instruction execution time		0.03125 µs (High-speed on-chip oscillator clock: f_{IH} = 32 MHz operation)	
		0.05 µs (High-speed system clock: f_{MX} = 20 MHz operation)	
		30.5 µs (Subsystem clock: f_{SUB} = 32.768 kHz operation)	
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.	
I/O port	Total	74	92
	CMOS I/O	64	82
	CMOS input	5	5
	CMOS output	1	1
	N-ch open-drain I/O (6 V tolerance)	4	4
Timer	16-bit timer	12 channels (TAU: 8 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)	
	Watchdog timer	1 channel	
	Real-time clock (RTC)	1 channel	
	12-bit interval timer	1 channel	
	Timer output	Timer outputs: 18 channels PWM outputs: 12 channels	
	RTC output	1 • 1 Hz (subsystem clock: f_{SUB} = 32.768 kHz)	

Note In the case of the 24 KB, this is about 23 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/G14 User's Manual).

(T_A = -40 to +85°C, 1.6 V $\leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq$ 5.5 V, $V_{SS} = EV_{SS0} = EV_{SS1}$ = 0 V) (3/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V_{IH1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0.8 EV_{DD0}		EV_{DD0}	V
	V_{IH2}	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V $\leq EV_{DD0} \leq$ 5.5 V	2.2		EV_{DD0}	V
			TTL input buffer 3.3 V $\leq EV_{DD0} <$ 4.0 V	2.0		EV_{DD0}	V
			TTL input buffer 1.6 V $\leq EV_{DD0} <$ 3.3 V	1.5		EV_{DD0}	V
	V_{IH3}	P20 to P27, P150 to P156		0.7 V_{DD}		V_{DD}	V
	V_{IH4}	P60 to P63		0.7 EV_{DD0}		6.0	V
	V_{IH5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0.8 V_{DD}		V_{DD}	V
Input voltage, low	V_{IL1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0		0.2 EV_{DD0}	V
	V_{IL2}	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V $\leq EV_{DD0} \leq$ 5.5 V	0		0.8	V
			TTL input buffer 3.3 V $\leq EV_{DD0} <$ 4.0 V	0		0.5	V
			TTL input buffer 1.6 V $\leq EV_{DD0} <$ 3.3 V	0		0.32	V
	V_{IL3}	P20 to P27, P150 to P156		0		0.3 V_{DD}	V
	V_{IL4}	P60 to P63		0		0.3 EV_{DD0}	V
	V_{IL5}	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$		0		0.2 V_{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (4/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = -10.0 mA	EV_{DD0} - 1.5			V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = -3.0 mA	EV_{DD0} - 0.7			V
			1.8 V ≤ EV_{DD0} ≤ 5.5 V, I_{OH1} = -1.5 mA	EV_{DD0} - 0.5			V
			1.6 V ≤ EV_{DD0} < 1.8 V, I_{OH1} = -1.0 mA	EV_{DD0} - 0.5			V
	V_{OH2}	P20 to P27, P150 to P156	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OH2} = -100 μA	V_{DD} - 0.5			V
Output voltage, low	V_{OL1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 20.0 mA			1.3	V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
			1.8 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 0.6 mA			0.4	V
			1.6 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL1} = 0.3 mA			0.4	V
	V_{OL2}	P20 to P27, P150 to P156	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60 to P63	4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 15.0 mA			2.0	V
			4.0 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 5.0 mA			0.4	V
			2.7 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 3.0 mA			0.4	V
			1.8 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 2.0 mA			0.4	V
			1.6 V ≤ EV_{DD0} ≤ 5.5 V, I_{OL3} = 1.0 mA			0.4	V

Caution **P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, P142 to P144 do not output high level in N-ch open-drain mode.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = 0 V)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 3	Basic operation	V_{DD} = 5.0 V		2.4		mA
						V_{DD} = 3.0 V		2.4		
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 3	Basic operation	V_{DD} = 5.0 V		2.1		
						V_{DD} = 3.0 V		2.1		
			HS (high-speed main) mode Note 5	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 3	Normal operation	V_{DD} = 5.0 V		5.1	8.7	mA
						V_{DD} = 3.0 V		5.1	8.7	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 3	Normal operation	V_{DD} = 5.0 V		4.8	8.1	
						V_{DD} = 3.0 V		4.8	8.1	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 3	Normal operation	V_{DD} = 5.0 V		4.0	6.9	
						V_{DD} = 3.0 V		4.0	6.9	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 3	Normal operation	V_{DD} = 5.0 V		3.8	6.3	
						V_{DD} = 3.0 V		3.8	6.3	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 3	Normal operation	V_{DD} = 5.0 V		2.8	4.6	
						V_{DD} = 3.0 V		2.8	4.6	
			LS (low-speed main) mode Note 5	f_{HOCO} = 8 MHz, f_{IH} = 8 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.3	2.0	mA
						V_{DD} = 2.0 V		1.3	2.0	
			LV (low-voltage main) mode Note 5	f_{HOCO} = 4 MHz, f_{IH} = 4 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.3	1.8	mA
						V_{DD} = 2.0 V		1.3	1.8	
			HS (high-speed main) mode Note 5	f_{MX} = 20 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		3.3	5.3	mA
						Resonator connection		3.4	5.5	
				f_{MX} = 20 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		3.3	5.3	
						Resonator connection		3.4	5.5	
				f_{MX} = 10 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		2.0	3.1	
						Resonator connection		2.1	3.2	
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		2.0	3.1	
						Resonator connection		2.1	3.2	
			LS (low-speed main) mode Note 5	f_{MX} = 8 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		1.2	1.9	mA
						Resonator connection		1.2	2.0	
				f_{MX} = 8 MHz Note 2, V_{DD} = 2.0 V	Normal operation	Square wave input		1.2	1.9	
						Resonator connection		1.2	2.0	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 4 T_A = -40°C	Normal operation	Square wave input		4.7	6.1	μA
						Resonator connection		4.7	6.1	
				f_{SUB} = 32.768 kHz Note 4 T_A = +25°C	Normal operation	Square wave input		4.7	6.1	
						Resonator connection		4.7	6.1	
				f_{SUB} = 32.768 kHz Note 4 T_A = +50°C	Normal operation	Square wave input		4.8	6.7	
						Resonator connection		4.8	6.7	
				f_{SUB} = 32.768 kHz Note 4 T_A = +70°C	Normal operation	Square wave input		4.8	7.5	
						Resonator connection		4.8	7.5	
				f_{SUB} = 32.768 kHz Note 4 T_A = +85°C	Normal operation	Square wave input		5.4	8.9	
						Resonator connection		5.4	8.9	

(**Notes** and **Remarks** are listed on the next page.)

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85°C, 2.7 V $\leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq$ 5.5 V, $V_{SS} = EV_{SS0} = EV_{SS1}$ = 0 V) (2/2)

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 2	t_{SIK1}	4.0 V $\leq EV_{DD0} \leq$ 5.5 V, 2.7 V $\leq V_b \leq$ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ	23		110		110		ns
		2.7 V $\leq EV_{DD0} <$ 4.0 V, 2.3 V $\leq V_b \leq$ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	33		110		110		ns
SIp hold time (from SCKp↓) Note 2	t_{KSI1}	4.0 V $\leq EV_{DD0} \leq$ 5.5 V, 2.7 V $\leq V_b \leq$ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ	10		10		10		ns
		2.7 V $\leq EV_{DD0} <$ 4.0 V, 2.3 V $\leq V_b \leq$ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	10		10		10		ns
Delay time from SCKp↑ to SOp output Note 2	t_{KSO1}	4.0 V $\leq EV_{DD0} \leq$ 5.5 V, 2.7 V $\leq V_b \leq$ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		10	ns
		2.7 V $\leq EV_{DD0} <$ 4.0 V, 2.3 V $\leq V_b \leq$ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

Remark 4. This value is valid only when CSI00's peripheral I/O redirect function is not used.

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS T_A = -40 to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications T_A = -40 to +105°C
R5F104xxGxx

Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

Caution 2. With products not provided with an EV_{DD0}, EV_{DD1}, EV_{SS0}, or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD}, or replace EV_{SS0} and EV_{SS1} with V_{SS}.

Caution 3. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G14 User's Manual.

Caution 4. Please contact Renesas Electronics sales office for derating of operation under T_A = +85 to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G14 is used in the range of T_A = -40 to +85°C, see **2. ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C)**.

Absolute Maximum Ratings **(2/2)**

Parameter	Symbols	Conditions		Ratings	Unit
Output current, high	I_{OH1}	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	-100	mA
	I_{OH2}	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	I_{OL1}	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	100	mA
	I_{OL2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T_A	In normal operation mode		-40 to +105	°C
		In flash memory programming mode			
Storage temperature	T_{stg}			-65 to +150	°C

Caution **Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Note 1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 3. When high-speed system clock and subsystem clock are stopped.

Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.

Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (64 MHz max.)

Remark 3. f_{IH}: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer is in operation.

Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.

Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.

Note 8. Current flowing during programming of the data flash.

Note 9. Current flowing during self-programming.

Note 10. For shift time to the SNOOZE mode, see **23.3.3 SNOOZE mode** in the RL78/G14 User’s Manual.

Note 11. Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{DAC} when the D/A converter operates in an operation mode or the HALT mode.

Note 12. Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2}, or I_{DD3} and I_{CMP} when the comparator circuit is in operation.

Note 13. A comparator and D/A converter are provided in products with 96 KB or more code flash memory.

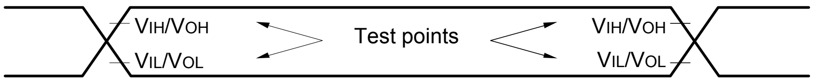
Remark 1. f_{IL}: Low-speed on-chip oscillator clock frequency

Remark 2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

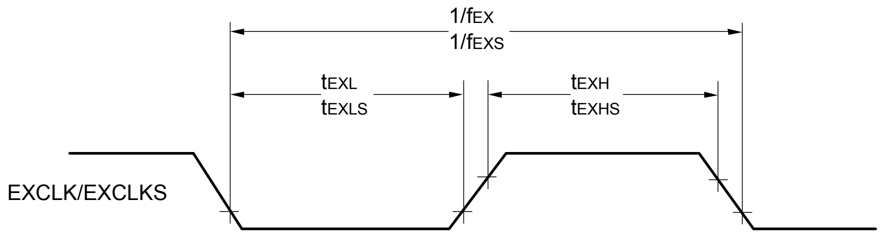
Remark 3. f_{CLK}: CPU/peripheral hardware clock frequency

Remark 4. Temperature condition of the TYP. value is T_A = 25°C

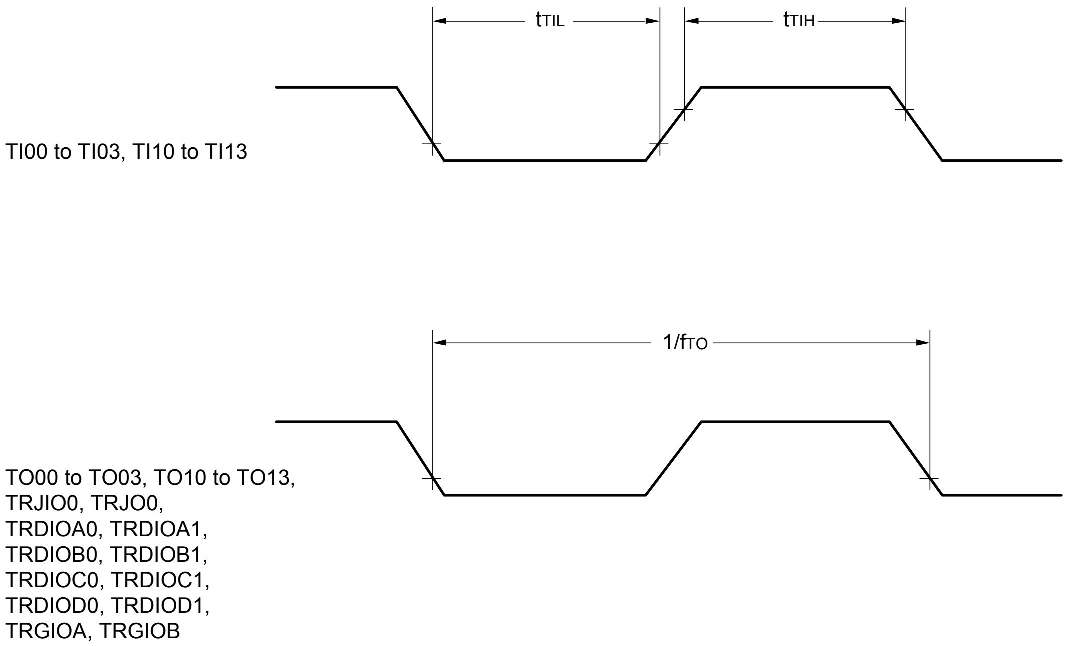
AC Timing Test Points



External System Clock Timing



TI/TO Timing



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions			HS (high-speed main) mode		Unit
					MIN.	MAX.	
Transfer rate		transmission	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			Note 1	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.6 Note 2	Mbps
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V			Note 3	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 4	Mbps
			2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			Note 5	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 6	Mbps

Note 1. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD0} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln\left(1 - \frac{2.2}{V_b}\right)\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln\left(1 - \frac{2.2}{V_b}\right)\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD0} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln\left(1 - \frac{2.0}{V_b}\right)\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln\left(1 - \frac{2.0}{V_b}\right)\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 4. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

Note 5. The smaller maximum transfer rate derived by using $f_{MCK}/12$ or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.4 V $\leq EV_{DD0} <$ 3.3 V and 1.6 V $\leq V_b \leq$ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln\left(1 - \frac{1.5}{V_b}\right)\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln\left(1 - \frac{1.5}{V_b}\right)\}}{\left(\frac{1}{\text{Transfer rate}}\right) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 6. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 5** above to calculate the maximum transfer rate under conditions of the customer.

Caution **Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

(**Remarks** are listed on the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ $4/f_{CLK}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	600		ns
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	1000		ns
			2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	2300		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		$t_{KCY1}/2$ - 150		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$t_{KCY1}/2$ - 340		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		$t_{KCY1}/2$ - 916		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		$t_{KCY1}/2$ - 24		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		$t_{KCY1}/2$ - 36		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		$t_{KCY1}/2$ - 100		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed two pages after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +105°C, 2.4 V $\le EV_{DD0} = EV_{DD1} \le V_{DD} \le$ 5.5 V, $V_{SS} = EV_{SS0} = EV_{SS1}$ = 0 V) (3/3)

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
SIp setup time (to SCKp↓) Note	t_{SIK1}	4.0 V $\le EV_{DD0} \le$ 5.5 V, 2.7 V $\le V_b \le$ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	88		ns
		2.7 V $\le EV_{DD0} <$ 4.0 V, 2.3 V $\le V_b \le$ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	88		ns
		2.4 V $\le EV_{DD0} <$ 3.3 V, 1.6 V $\le V_b \le$ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	220		ns
SIp hold time (from SCKp↓) Note	t_{KSI1}	4.0 V $\le EV_{DD0} \le$ 5.5 V, 2.7 V $\le V_b \le$ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	38		ns
		2.7 V $\le EV_{DD0} <$ 4.0 V, 2.3 V $\le V_b \le$ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	38		ns
		2.4 V $\le EV_{DD0} <$ 3.3 V, 1.6 V $\le V_b \le$ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	38		ns
Delay time from SCKp↑ to SOp output Note	t_{KSO1}	4.0 V $\le EV_{DD0} \le$ 5.5 V, 2.7 V $\le V_b \le$ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		50	ns
		2.7 V $\le EV_{DD0} <$ 4.0 V, 2.3 V $\le V_b \le$ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		50	ns
		2.4 V $\le EV_{DD0} <$ 3.3 V, 1.6 V $\le V_b \le$ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		50	ns

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = VDD Reference voltage (-) = VSS	Reference voltage (+) = VBGR Reference voltage (-)= AVREFM
ANI0 to ANI14	Refer to **3.6.1 (1)**.	Refer to **3.6.1 (3)**.	Refer to **3.6.1 (4)**.
ANI16 to ANI20	Refer to **3.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **3.6.1 (1)**.		—

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V ≤ AVREFP ≤ VDD ≤ 5.5 V, VSS = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	tCONV	10-bit resolution Target pin: ANI2 to ANI14	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	µs
			2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	µs
			2.4 V ≤ VDD ≤ 5.5 V	17		39	µs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ VDD ≤ 5.5 V	2.375		39	µs
			2.7 V ≤ VDD ≤ 5.5 V	3.5625		39	µs
			2.4 V ≤ VDD ≤ 5.5 V	17		39	µs
Zero-scale error Notes 1, 2	EZS	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±1.5	LSB
Analog input voltage	VAIN	ANI2 to ANI14		0		AVREFP	V
		Internal reference voltage output (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode)		VBGR Note 4			V
		Temperature sensor output voltage (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode)		VTMPS25 Note 4			V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When AVREFP < VDD, the MAX. values are as follows.

Overall error:	Add ±1.0 LSB to the MAX. value when AVREFP = VDD.
Zero-scale error/Full-scale error:	Add ±0.05%FSR to the MAX. value when AVREFP = VDD.
Integral linearity error/ Differential linearity error:	Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

Note 4. Refer to **3.6.2 Temperature sensor characteristics/internal reference voltage characteristic**.

Rev.	Date	Description	
		Page	Summary
2.00	Oct 25, 2013	112 to 169	Addition of CHAPTER 3 ELECTRICAL SPECIFICATIONS
		171 to 187	Modification of 4.1 30-pin products to 4.10 100-pin products
3.00	Feb 07, 2014	All	Addition of products with maximum 512 KB flash ROM and 48 KB RAM
		1	Modification of 1.1 Features
		2	Modification of ROM, RAM capacities and addition of note 3
		3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14
		6 to 8	Addition of part number
		15, 16	Modification of 1.3.6 48-pin products
		17	Modification of 1.3.7 52-pin products
		18, 19	Modification of 1.3.8 64-pin products
		20	Modification of 1.3.9 80-pin products
		21, 22	Modification of 1.3.10 100-pin products
		35, 37, 39, 41, 43, 45, 47	Modification of operating ambient temperature in 1.6 Outline of Functions
		42, 43	Addition of table of 48-pin, 52-pin, 64-pin products (code flash memory 384 KB to 512 KB)
		46, 47	Addition of table of 80-pin, 100-pin products (code flash memory 384 KB to 512 KB)
		65 to 68	Addition of (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products
		118	Modification of 2.7 Data Memory Retention Characteristics
		137 to 140	Addition of (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products
		180	Modification of 3.7 Data Memory Retention Characteristics
		189, 190	Addition and modification of 4.6 48-pin products
		191	Modification of 4.7 52-pin products
		193 to 195	Addition and modification of 4.8 64-pin products
		198, 199	Addition and modification of 4.9 80-pin products
		201, 202	Addition and modification of 4.10 100-pin products
3.20	Jan 05, 2015	p.2	Deletion of R5F104JK and R5F104JL from the list of ROM and RAM capacities and modification of note
		p.6	Deletion of ordering part numbers of R5F104JK and R5F104JL from 52-pin plastic LQFP package in 1.2 Ordering Information
		p.6 to 8	Deletion of note 2 in 1.2 Ordering Information
		p.17	Deletion of note 2 in 1.3.7 52-pin products
		p.36, 39, 42, 45, 48, 50, 52	Modification of description in 1.6 Outline of Functions
		p.46, 48	Deletion of description of 52-pin in 1.6 Outline of Functions
		p.47	Modification of note of 1.6 Outline of Functions
		p.62, 64, 66, 68, 70, 72	Modification of specifications in 2.3.2 Supply current characteristics